

Please amend the subject application as follows:

IN THE SPECIFICATION:

Please amend the paragraph beginning at page 2, line 7 and ending at page 2, line 15, to read as follows:

--To read the logic state of a magnetic memory cell, the MRAM device applies a sense current and a reference current to a target cell and a reference cell, respectively. A voltage drop occurs at both ends of the target cell and the reference cell depending on the respective resistance values of the cells. The voltages of the cells are compared with each other to determine a logic state of the target cell. FIG. 1 shows a conventional 32Kb MRAM memory block including a midpoint reference generator therein. FIG. 1 originates from FIG. 7 of a paper reporting the demonstration of MRAM from the 2002 VLSI ~~Symposia~~ Symposia on Technology and Circuits.--

Please amend the paragraph beginning at page 10, line 7 and ending at page 10, line 12, to read as follows:

--According to the data value of the selected memory cell, current $i(H)$ or $i(L)$ flows to the data line ~~in line~~. In addition, constant current $i_T - (i(H) + i(L))/2$ flows to the reference data line without a requiring adjustment to the level of the bitline clamp voltage V_{REF} . As a result, the operation of a sense amplifier 380 of comparing the current $i_T - i(H)$ or $i_T - i(L)$ of the data line to the current $i_T - (i(H) + i(L))/2$ of the reference data line is more stable and efficient.--